



N-CHANNEAL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _{D MAX} T _A = +25°C
12V	$29m\Omega$ @ $V_{GS} = 4.5V$	5.6A
	$34m\Omega @ V_{GS} = 2.5V$	5.1A
	44mΩ @ V _{GS} = 1.8V	4.5A
	65mΩ @ V _{GS} = 1.5V	3.7A

Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description

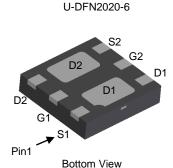
This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

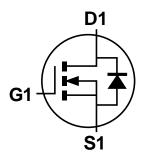
Applications

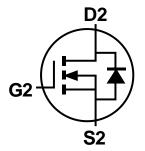
- Load Switch
- Power Management Functions
- Portable Power Adaptors

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)







Q1 N-CHANNEL MOSFET

Q2 N-CHANNEL MOSFET

Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1029UFDB -7	U-DFN2020-6	3000/Tape & Reel
DMN1029UFDB -13	U-DFN2020-6	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



D5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	201	5	2016		2017	20	18	2019		2020	2	2021
Code	С		D		E		=	G		Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	12	V	
Gate-Source Voltage	V_{GSS}	±8	V		
Continuous Prain Current (Note 5) V 45V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	5.6 4.4	Α
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t < 5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	7.2 5.8	Α
Maximum Continuous Body Diode Forward Curre	ent (Note 5)	I _S	1	Α	
Pulsed Drain Current (10 µs pulse, Duty Cycle = 1	lsed Drain Current (10μs pulse, Duty Cycle = 1%)		I _{DM}	20	Α
Avalanche Current (L = 0.1mH)		I _{AS}	15	Α	
Avalanche Energy (L = 0.1mH)	•	E _{AS}	12	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	Steady State	0	1.4	W	
Total Fower Dissipation (Note 5)	t < 5s	P_{D}	2.2	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	0	91		
Thermal Resistance, Junction to Ambient (Note 5)	t < 5s	$R_{ heta JA}$	55	°C/W	
Thermal Resistance, Junction to Case	$R_{ heta JC}$	20			
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

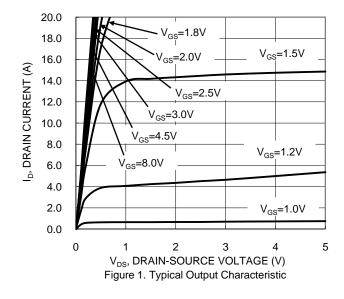
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	12	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		_	1.0	μΑ	$V_{DS} = 12V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	0.4	_	1	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		_	17	29		$V_{GS} = 4.5V, I_D = 5A$	
Static Drain-Source On-Resistance	<u></u>	_	20	34	mΩ	$V_{GS} = 2.5V, I_D = 4.6A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	24	44	11122	$V_{GS} = 1.8V, I_D = 4.1A$	
		_	30	65		$V_{GS} = 1.5V, I_D = 2A$	
Diode Forward Voltage	V_{SD}	_	0.6	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}		914	_	pF	.,	
Output Capacitance	Coss	_	132	_	pF	$V_{DS} = 6V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	119	_	pF	1 = 1.000112	
Gate Resistance	R_g	_	1.26	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	0	_	10.5	_	nC		
Total Gate Charge (V _{GS} = 8V)	Q_g	_	19.6	_	nC],, o,, i, o,5,	
Gate-Source Charge	Qgs	_	1.2	_	nC	$V_{DS} = 6V, I_{D} = 6.5A$	
Gate-Drain Charge	Q_{qd}		1.6	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	5.0	_	ns		
Turn-On Rise Time	t _R	_	10.5	_	ns	$V_{DD} = 6V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}		16.6	_	ns	$R_L = 1.2\Omega$, $R_G = 1\Omega$	
Turn-Off Fall Time	t _F	_	4.1	_	ns	7	

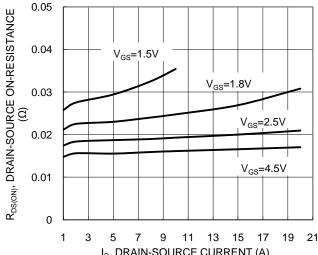
Notes: 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

6. Short duration pulse test used to minimize self-heating effect.

7. Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

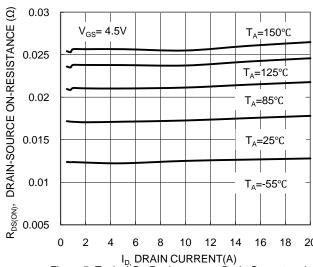
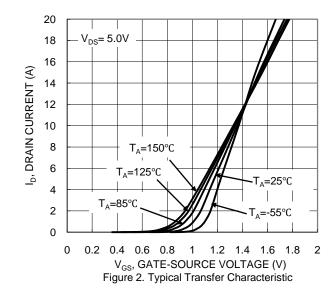
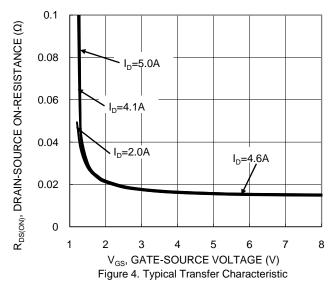


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





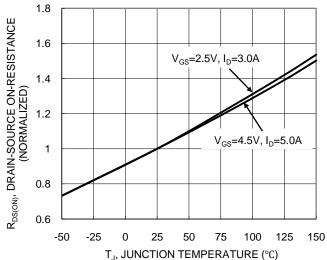


Figure 6. On-Resistance Variation with Temperature



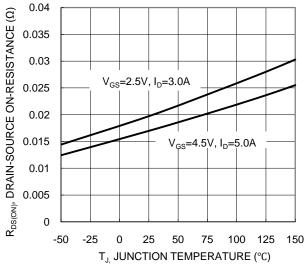
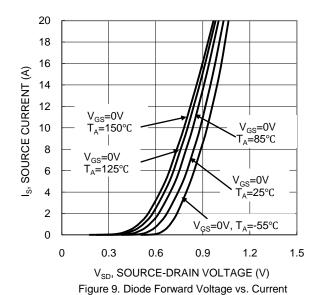


Figure 7. On-Resistance Variation with Temperature



(S) BORT-SOURCE VOLTAGE (S) VDS=6V, ID=6.5A

10

Qg, TOTAL GATE CHARGE (nC) Figure 11. Gate Charge

15

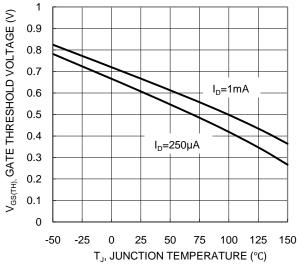
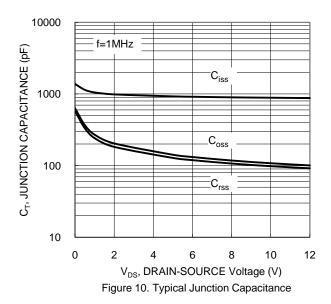
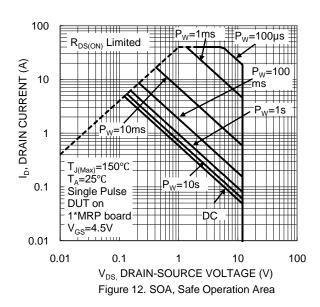


Figure 8. Gate Threshold Variation vs. Junction Temperature



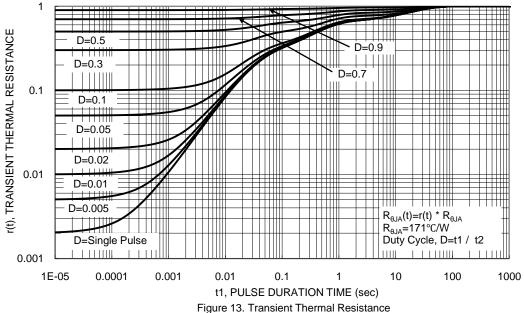


0

8

20

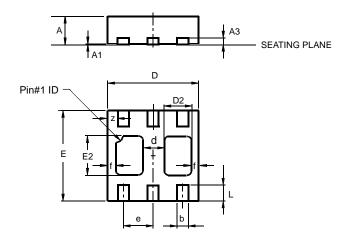




rigure 15. Transient menna resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

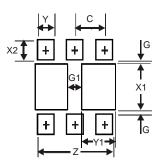


U-DFN2020-6 Type B								
Dim	Min Max Typ							
Α	0.545	0.605	0.575					
A1	0	0.05	0.02					
A3			0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
d	_	_	0.45					
D2	0.50	0.70	0.60					
е	_	_	0.65					
E	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
f			0.15					
L	0.25	0.35	0.30					
Z			0.225					
All Dimensions in mm								



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Υ	0.37
Y1	0.70
С	0.65

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